

HIRAMOTO-KOBAYASHI LAB.





Department of Informatics and Electronics

Integrated Device Engineering – Integrated Nanoelectronics

http://vlsi.iis.u-tokyo.ac.jp https://nano-lsi.iis.u-tokyo.ac.jp

Department of Electrical Engineering and Information

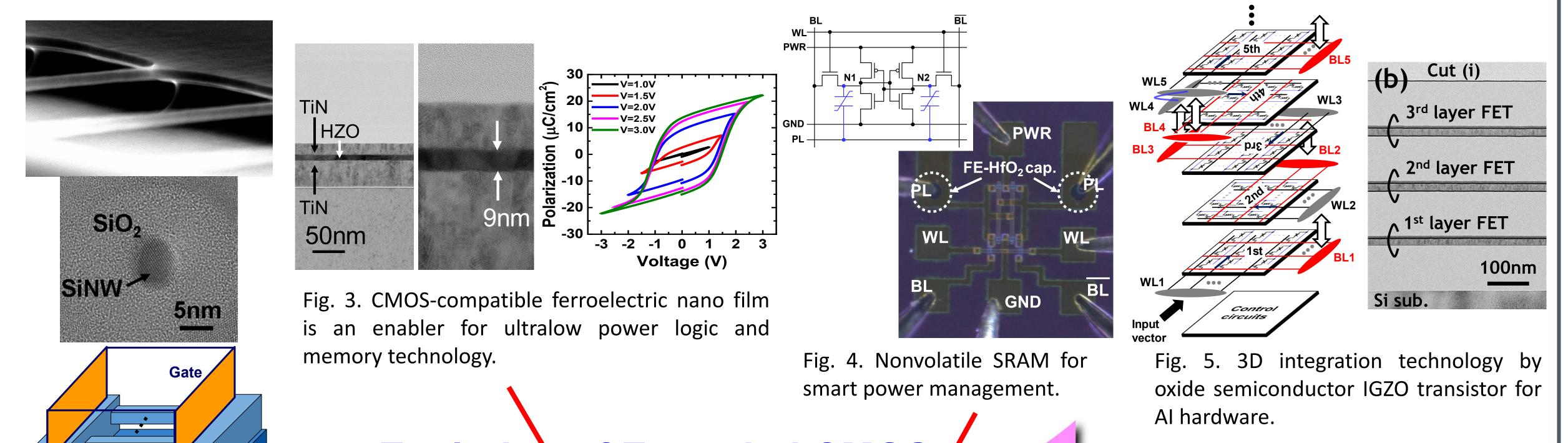
Towards VLSIs integrating everything

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Very large scale integration (VLSI) is the basis of contemporary advanced IT society. Hiramoto/Kobayashi Lab. aims at solving worldwide problems by the technological innovation of future integrated nanoelectronics from the device side. Prof. M. Kobayashi, formerly a researcher in IBM Watson Research working on advanced semiconductor technology, joined the lab in 2014. Based on the vision in Fig. A, we are pursuing the extreme form of integrated nanodevices.



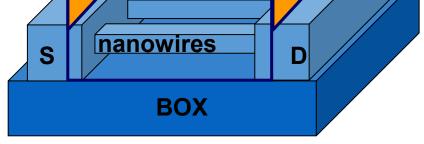


Fig. 1. Silicon nano-wire transistors were fabricated and the quantum effects were evaluated.

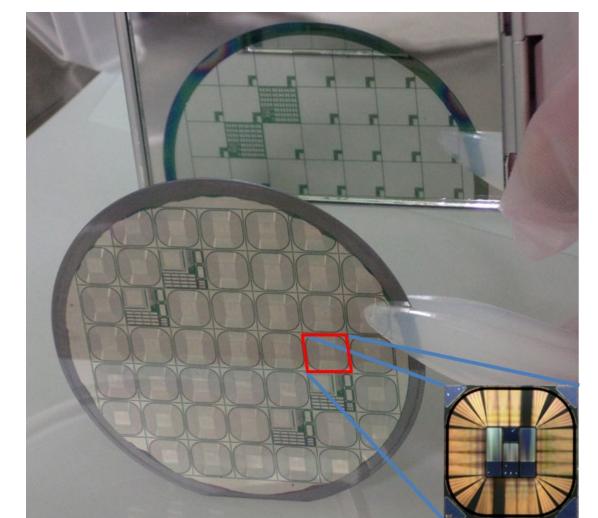


Fig. 2. The silicon power device project was initiated. The current density of IGBT was improved by the scaling concept at blocking voltage of 3000V. The doublegate IGBT was also demonstrated.



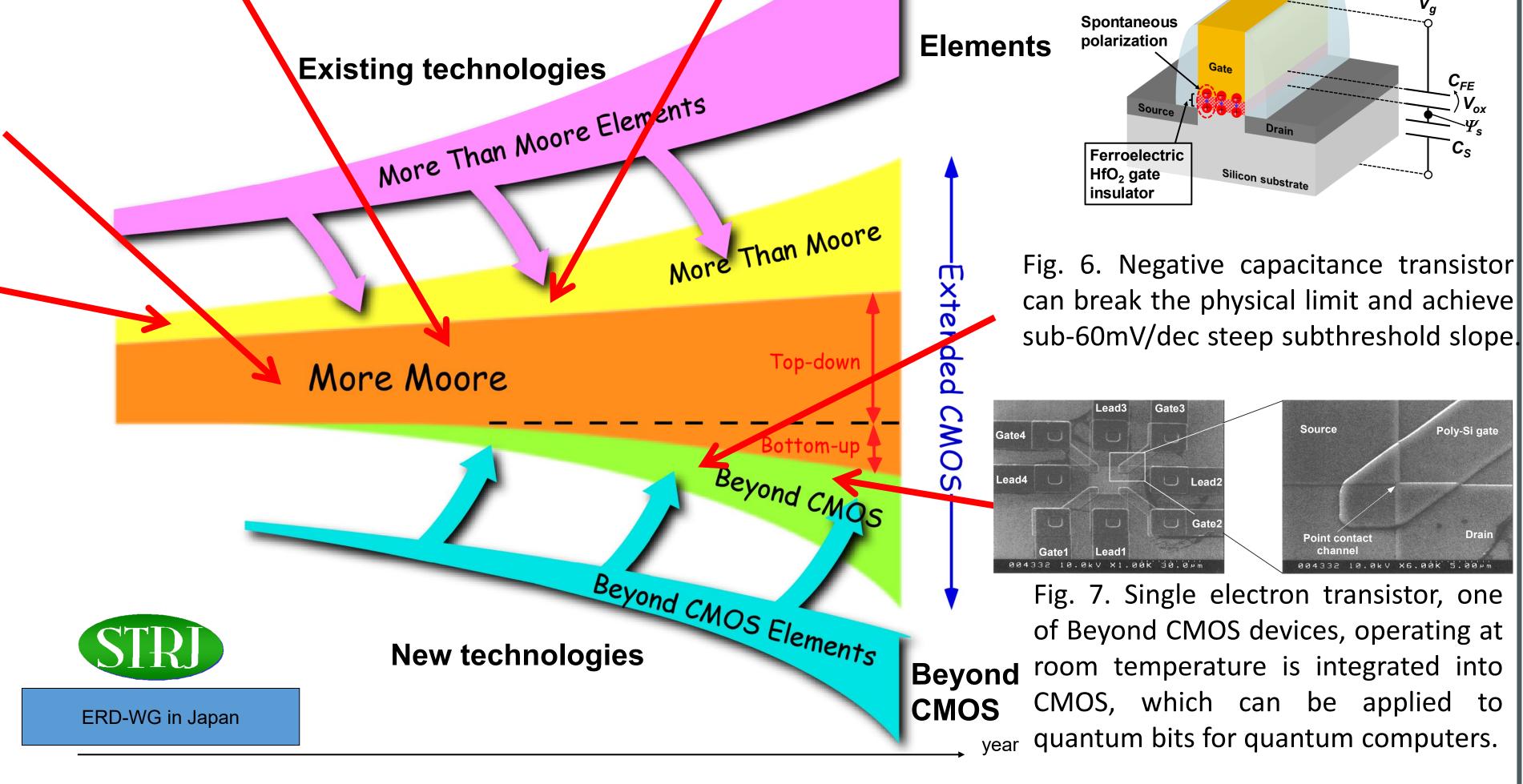


Fig. A. A vision map of the integrated nanoelectronics, drawn by Prof. Hiramoto in Semiconductor Technology Roadmap Committee of Japan (STRJ). A new field of "Extended CMOS" will be created by integrating "Beyond CMOS" and "More Than Moore" into CMOS base



